2SK2593J

Silicon N-channel junction FET

For low-frequency amplification For switching circuits

Features

- Low noise figure NF
- High gate-drain voltage (source open) V_{GDO}
- SSMini type package, allowing downsizing of the equipment and automatic insertion through the tape packing.

Absolute Maximum Ratings $T_a = 25^{\circ}C$

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Parameter	Symbol	Rating	Unit			
Drain-sourse voltage	V _{DS}	55	V			
Gate-drain voltage (Source open)	V _{GDO}	-55	V			
Gate-source voltage (Drain open)	V _{GSO}	-55	V			
Drain current	ID	30	mA			
Gate current	I _G	10	mA			
Power dissipation	PD	125	mW			
Channel temperature	T _{ch}	125	°C			
Storage temperature	T _{stg}	-55 to +125	°C			

- Package
- Code
- SSMini3-F1
- Pin Name
 - 1: Source
 - 2: Drain
 - 3: Gate
- Marking Symbol: 2B

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

V _{GDS}	$I_{G} = -100 \ \mu A, V_{DS} = 0$				
-	6 1 25	-55			V
I _{DSS}	$V_{DS} = 10 \text{ V}, V_{GS} = 0$	1.0		6.5	mA
I _{GSS}	$V_{GS} = -30 \text{ V}, V_{DS} = 0$			-10	nA
V _{GSC}	$V_{DS} = 10 \text{ V}, I_D = 10 \mu\text{A}$			-5	V
Y _{fs}	$V_{DS} = 10 \text{ V}, I_D = 5 \text{ mA}, f = 1 \text{ kHz}$	2.5	7.5		mS
C _{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		6.5		pF
C _{rss}			1.9		pF
NF	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 100 \text{ Hz}$		2.5		dB
	$\begin{array}{c} I_{GSS} \\ V_{GSC} \\ Y_{fs} \\ C_{iss} \\ \hline \\ C_{rss} \end{array}$	$\begin{array}{c c} I_{GSS} & I_{DS} = -30 \ V, \ V_{DS} = 0 \\ \hline V_{GSC} & V_{DS} = 10 \ V, \ I_D = 10 \ \mu A \\ \hline \ Y_{fs} & V_{DS} = 10 \ V, \ I_D = 5 \ mA, \ f = 1 \ kHz \\ \hline C_{iss} & V_{DS} = 10 \ V, \ V_{GS} = 0, \ f = 1 \ MHz \end{array}$	$\begin{array}{c c} I_{GSS} & V_{GS} = -30 \ V, \ V_{DS} = 0 \\ \hline V_{GSC} & V_{DS} = 10 \ V, \ I_D = 10 \ \mu A \\ \hline \ Y_{fs} & V_{DS} = 10 \ V, \ I_D = 5 \ mA, \ f = 1 \ kHz \\ \hline C_{iss} & V_{DS} = 10 \ V, \ V_{GS} = 0, \ f = 1 \ MHz \\ \hline \hline NF & V_{DS} = 10 \ V, \ V_{GS} = 0, \ f = 100 \ Hz \end{array}$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

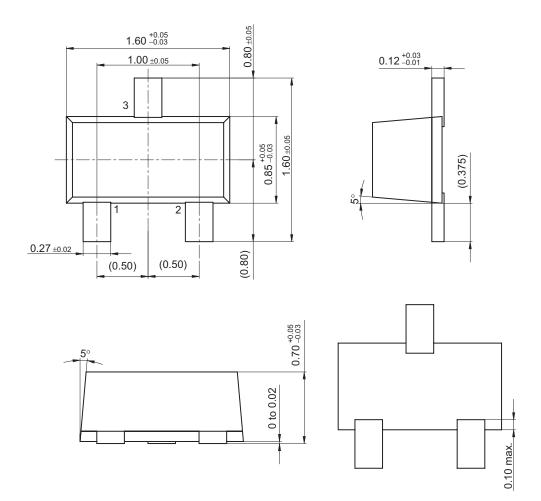
2. *: Rank classification

Rank	Р	Q
I _{DSS} (mA)	1.0 to 3.0	2.0 to 6.5

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SSMini3-F1

Unit: mm



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